**2016 Rover Battery System**

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**Introduction**

The battery system for the 2016 rover encompasses everything necessary for the battery pack’s operation, which includes the battery management system, the battery charger, and the battery cells themselves.

**Battery Pack**

**Battery Management System**

**Battery Charger**

An integrated charger for the battery pack is desired in order to charge the batteries at their rated-charging speed and to simplify the charging process for the end-user. The preliminary charger will accept a DC-input greater than pack voltage for a buck-converter based charger. A future revision of the charger could be a buck-boost converter that would also accept charging voltages below pack voltage.

**Charging Requirements**

The selected cells are rated for two charging algorithms: a standard charge and a fast charge. As their names indicate, the standard charging algorithm is slower, but results in increased cell lifetime; while the fast charge is significantly faster but will reduce cell lifetime.

The standard charging algorithm consists of two phases: the constant current (CC) phase and the constant voltage phase (CV). For a standard charge, CC charging first takes place at 1250mA (per parallel cell), then CV charging takes at 4.2V (per series cell) until charging current tapers to 50mA per cell. For a fast charge, CC charging first takes place at 4000mA (per parallel cell), then CV charging takes at 4.2V (per series cell) until charging current tapers to 100mA per cell. After fast charging the batteries must rest for 10 minutes.

Since the fast charging algorithm places the greatest demand on the battery charger, it will be used for determining battery charger requirements. For the proposed 10 parallel/8 series (10p8s) battery pack, the minimum pack voltage will be 20V and the maximum pack voltage will be 33.6V. Thus the charger must be capable of constant voltage charging at 33.6V. Since there are ten cells in parallel, the charger must be capable of sourcing 40A during CC charging. The worst-case power draw on the charger occurs during a 33.6V, 40A charging period (an unlikely load point for the battery pack), which is equal to 1344W. Design goals for the charger are summarized in table 1 below.

|  |  |  |  |  |
| --- | --- | --- | --- | --- |
| **Parameter** | **Minimum** | **Nominal** | **Maximum** | **Units** |
| Output Voltage | 20.0 |  | 33.6 | V |
| Output Current | 12.5 |  | 40.0 | A |
| Input Voltage | 35 |  | 50 | V |
| Rated Power |  | 1350 |  | W |
| Efficiency | 85 | 95 |  | % |
| Weight |  | 200 | 1000 | g |
| Board Area |  |  | 24 | Sq. in. |

**Table 1 –** Charger Design Parameters

**Buck-Converter Design**

>Include a switching frequency vs. required inductance graph

**Inductor Selection**

The selected inductor is largely dependent on the selected switching frequency for the converter. Higher switching frequencies lead to higher switching losses and create more stringent requirements for the converter’s MOSFET switches and MOSFET drivers, however allow for the use of smaller magnetics. Lower switching frequencies require an inductor of higher rated inductance and thus a larger, heavier inductor. Inductors for various switching frequencies are presented in this section.

Based on the analysis in the previous section, a switching frequency of in the range of 50kHz to 500kHz is likely. The requirements for inductors for frequencies in this range are presented in table 2 below.

|  |  |  |  |  |
| --- | --- | --- | --- | --- |
| **Parameter** | **50kHz Inductor** | **125kHz Inductor** | **250kHz Inductor** | **500kHz Inductor** |
| Inductance (μH) | 132 | 88 | 44 | 22 |
| RMS Current (A) | 40 | 40 | 40 | 40 |
| Saturation Current (A) | 40 | 40 | 40 | 40 |
| Ripple Current (A) |  |  |  |  |

**Table 2 –** Inductor Requirements for Various Switching Frequencies.

Various suppliers were searched for inductors that meet the above requirements. The selected inductor for each switching frequencies was selected by best meeting the required electrical characteristics while minimizing cost, weight, and size. Possible inductors are presented in table 3 below. Values for the table were derived from the manufacturer datasheet tables and the curves shown in figures 1, 2, and 3.

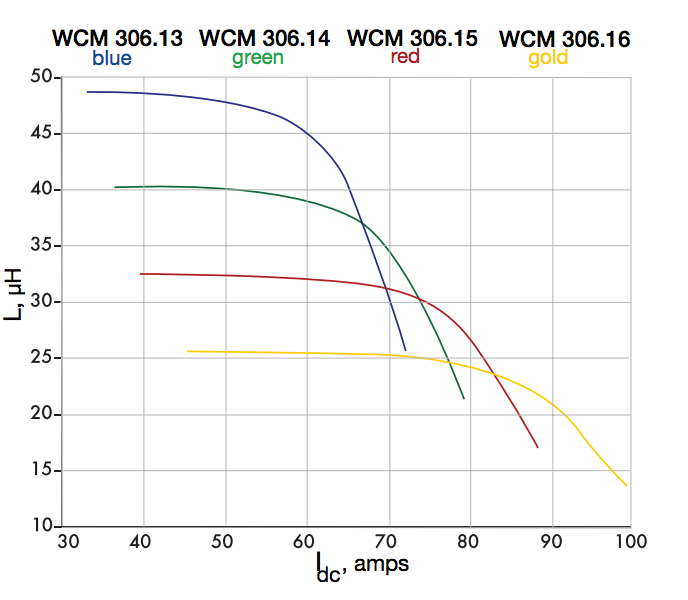
|  |  |  |  |  |
| --- | --- | --- | --- | --- |
| **Parameter** | **50kHz Inductor** | **125kHz Inductor** | **250kHz Inductor** | **500kHz Inductor** |
| **Part Number** | WCM 306-8 | WCM 306-10 | WCM 306-13 | AGP4233-223ME |
| **Supplier** | West Coast Magnetics | West Coast Magnetics | West Coast Magnetics | Coilcraft |
| **Price ($)** |  |  |  |  |
| **Inductance (μH)** | 131 | 91 | 49 | 22 |
| **Inductance Tolerance** |  |  |  | +/- 10% |
| **Weight (g)** | 1000 | 1000 | 1000 | 135 |
| **DCR (mOhms)** | 2.80 | 1.89 | 1.03 | 2.95 |
| **Size - Length, Width, Height (cm)** | 7.75 x 7.24 x 7.62 | 7.75 x 7.24 x 7.62 | 7.75 x 7.24 x 7.62 | 4.22 x 3.58 x 2.80 |
| **RMS Current (A)** | 33.0 | 39.0 | 55.0 | 34.0 |
| **Saturation Current, 10% (A)** | 37 | 45 | 60 | 32.8 |
| **Saturation Current, 20% (A)** | 39 | 47 | 65 | 35.4 |
| **Saturation Current, 30% (A)** | 42 | 50 | 67 | 36.6 |
| **Ripple Current (A)** |  |  |  |  |
| **Temperature (C)** |  |  |  | 125 |

**Table 3 –** Selected Inductor Characteristics for Various Switching Frequencies[1][2].

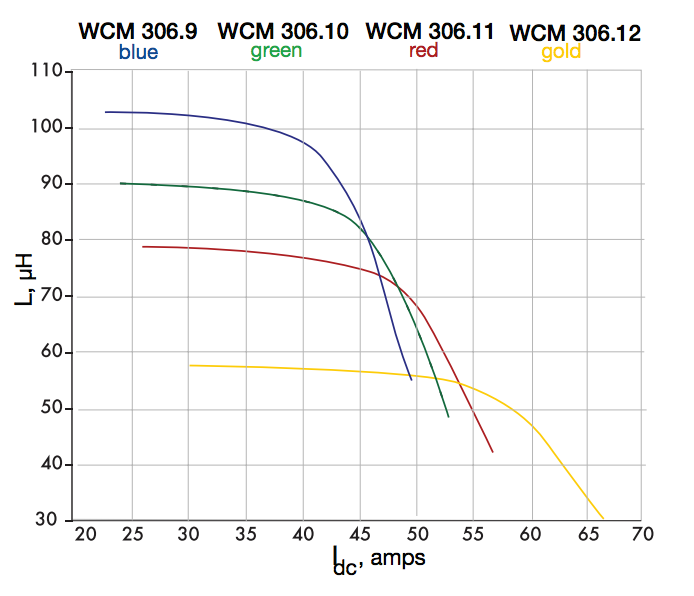
The two best inductors for this application are the WCM-306-10 (a 91uH inductor produced by West Coast Magnetics) and the AGP4233-233ME (a 22 uH inductor produced by Coilcraft).

The WC Magnetics inductor is well suited for this application because it allows for a reasonable switching frequency (125kHz) while still meeting the current requirements of the converter (the 39.0Arms is the limiting current rating; the core will not saturate within the converter’s operating limits). Unfortunately this inductor is quite large, weighing 1kg and having a board surface area of 56.11cm2 (8.70in2). This makes the inductor ideal for an off-rover charger; however, it may prove to be too large for an integrated charger.

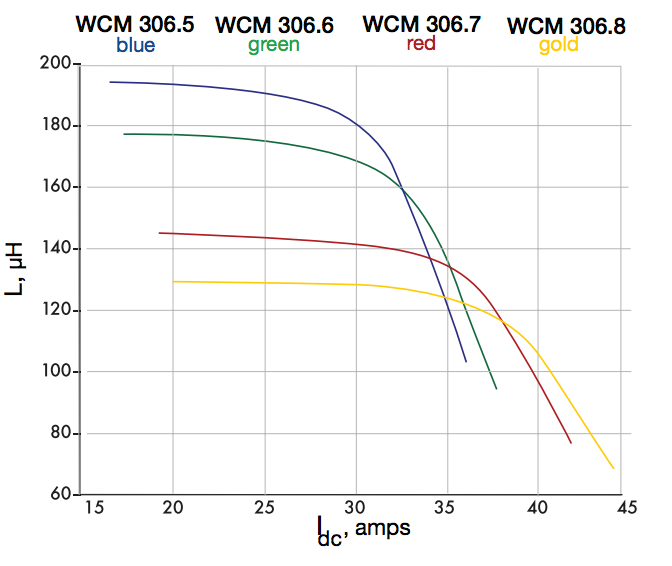
The Coilcraft inductor is also well-suited for this application largely due to small-size. It weighs only 135 grams and uses only 15.10cm2 (2.34 in2) of board space. This is 86% savings in weight and 73% savings in volume compared to the WC Magnetics inductor. Unfortunately this inductor is not capable of supporting the full rated current of the charger, limited by a 34.0Arms current and a 32.8A saturation current for a 10% loss of inductance. (More detailed analysis is required to demonstrate this inductors performance over various charger operating points due to the lower saturation current.)



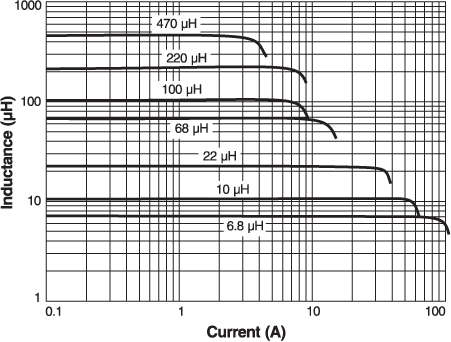
**Figure 1 –** Saturation Current for Inductor WCM 306.13.



**Figure 2 –** Saturation Current for Inductor WCM 306.10.



**Figure 3 –** Saturation Current for Inductor WCM 306.8.



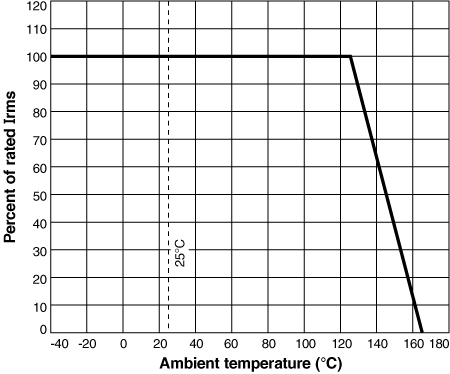
**Figure 4 –** Saturation Current for the Coilcraft Inductors.

There are two major sources of inductor losses: AC-current induced core losses and DC equivalent-resistance heat losses. For each of the selected inductors the core losses are negligible compared to the resistive heating loses, so they are ignored here. The resistive losses may be calculated for both inductors using the maximum RMS current of the charger and the equivalent DC resistance of the inductor:

For the Coilcraft inductor:

For the selected WC Magnetics inductor:

For the Coilcraft inductor, the manufacturer’s website indicates this would lead to approximately a 45°C increase in inductor temperature. Furthermore, the temperature derating curve (*see figure 4*) indicates that this temperature rise would not be an issue for a wide range of ambient temperatures. WC Magnetics does not publish data on their inductors’ thermal resistance, so there is not a direct method to calculate this part’s temperature rise above ambient; however, it is possible to assume it would remain within normal operating conditions as 40A is far below the part’s rated RMS current.



**Figure 4 –** RMS Current Temperature Derating Curve for AGP4233-223ME [3].

**MOSFET Switch Selection**

As discussed in the section on inductor selection, there is a trade-off between switching frequency, inductor requirements, and MOSFET requirements.

For this type of switching converter, the MOSFET is a large source of losses. Losses occur largely in two regions of the switch’s operation: the linear region when the switch is between its “on” and “off” states, and in the saturation region when the switch is “fully on.” Losses in saturation mode are most easily modeled by an equivalent on-state resistance known as the “rds(on).” Losses in the linear mode are more complex to model and much greater than those when the MOSFET is in the saturation region. Therefore it is important to minimize the time that the MOSFET operates in the linear region. This time is dictated by a variety of factors, including gate capacitance, body diode capacitance, and ajlkdfjakd [4]. Additionally the functionality of the MOSFET will depend on its thermal characteristics. Potential MOSFETs for this application are presented in table 4 below.

|  |  |  |  |  |
| --- | --- | --- | --- | --- |
| **Part Number** | **CSD18532KCS** | **IRFH7191** | **IRFH7188** | **IRFH7185** |
| **Manufacturer** | Texas Instruments | International Rectifier | International Rectifier | International Rectifier |
| **Package** | TO-220 | PQFN 5x6 B/E | PQFN 5x6 B/E | PQFN 5x6 B/E |
| **Price ($/1 unit)** | $2.79 | $2.87 | $2.43 | $3.64 |
| **VBRDSS (V)** | 60 | 100 | 100 | 100 |
| **VGS,Max (V)** | 20 | 20 | 20 | 20 |
| **RDS(on) (mOhms)** | **4.2** | **8** | **6** | **5.2** |
| **Qg (nC)** | **44** | **26** | **33** | **36** |
| **Qgd (nC)** | 6.9 | 8.3 | 11 | 11 |
| **Id @ T=25C (A)** | 100 | 80 | 105 | 123 |
| **Ciss (pF)** | 3900 | 1685 |  |  |
| **Coss (pF)** | 470 | 836 |  |  |
| **Qrr - Diode (nC)** | 127 | 126 |  |  |
| **RΘJC (°C/W)** | 0.6 | 1.2 |  |  |
| **RΘJA (°C/W)** | 62 | 35 |  |  |
| **Q\*R** | 185 | 208 | 198 | 187 |

**Table 4 –** Comparison of potential switching MOSFETS with a Q\*R figure of merit; unit price collected from Digikey [5][6][7][8].

With modern FET technology, the selection of a MOSFET capable of sustaining 40A continuous in the on-state is trivial. A buck-converter by nature, however, will rarely operate with the switching FET continuously in the on-state. During transitions between the on- and off-states the FET will operate in a linear/triode region in which significantly greater switching losses will occur. Therefore, in order to minimize the total switching losses, it is essential that the MOSFET remain in the linear region of operation for the shortest period of time possible. This transition time is dictated by how quickly the gate-to-source voltage can be transitioned by the driver circuit. In ideal conditions, this is nearly instantaneous. A real-world trade off in the construction of high-current FETs, however, is the presence of a significant capacitance at the gate of the MOSFET, which contains a large charge that must be transferred by the driver circuit. For MOSFETs with a large gate charge this can require pulses of many amperes to switch the MOSFET quickly. If this switching transition is not sufficiently minimized, the converter will incur significant switching losses and the MOSFET will overheat. Typically, there is a tradeoff between minimizing the Rds,ON and the gate charge of a MOSFET. Additionally, some manufacturers produce MOSFETs with low gate charges specifically for high-speed switching applications.

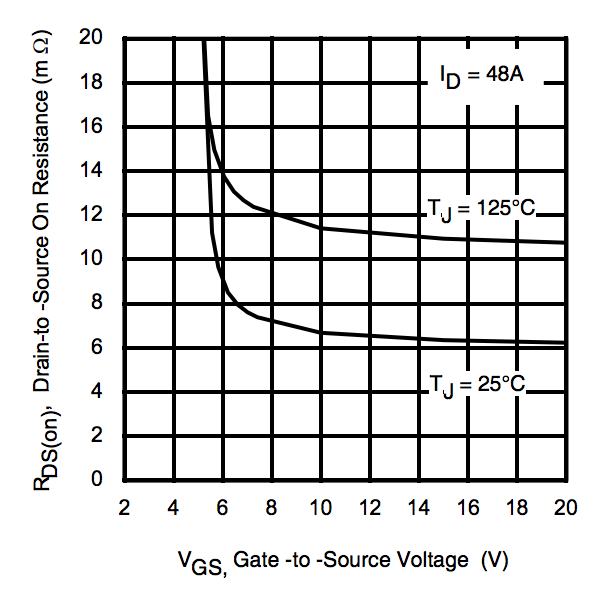
Of the MOSFETs listed in table 4, the IRFH7191 is best suited for this application. All of the MOSFETs have a similar Q\*R figure of merit, which indicates the switches performance for both minimizing loss during operation in the saturation region and it ability to be switched between the on and off states quickly so as to minimize time in the linear region of operation [12]. As the RDS(on) values of all the MOSFETs were appropriate for this application, the 7191 was selected for its especially low gate charge and input capacitance; allowing it to perform well during high speed switching.

Power losses in this switch may be estimated by analyzing its performance independently in two operating regions: the linear/triode region during switching; and the saturation region during its on-state [4]. In the on-state the MOSFETs losses may simply be modeled as a series resistance, equal to the value of RDS(on) provided in the datasheet. It is important to note that the value of RDS(on) also varies over temperature, so it is important to account for this in analysis. This characteristic is shown in figure 5 below.

Assuming that the driver circuit ensures MOSFET operation in full saturation (by ensuring VGS is greater than approximately 8V), then at 25°C it is reasonable to assume an RDS(on) of approximately 6.5mΩ, and at 125°C it is reasonable to assume an RDS(on) of 11mΩ. Note that there is a significant increase in switching losses as the FET’s temperature increases. Standard full-load conditions for this charger are specified to be 40A (although lower limits may exist for some inductors due to core saturation). Using these values, the power loss in the FET may be calculated for both temperature conditions:

For 25°C:

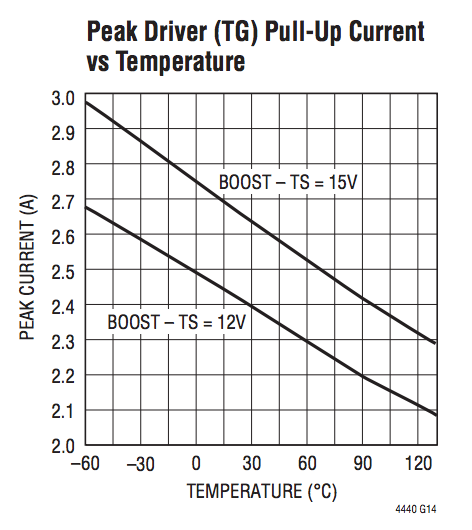
And for 125°C:



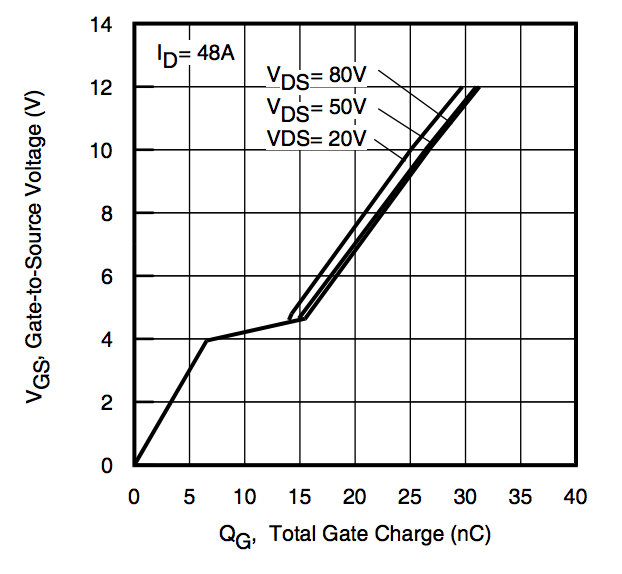
**Figure 5 –** IRFH7191 RDS(on) vs. VGS at 25°C and 125°C.

Analysis of switching losses in the linear region is more complicated, as there are many sources of switching losses [4]. The following sources of switching losses may be calculated with the parameters of the MOSFET which are made available from the manufacturer: turn-off losses, turn-on losses, body diode recovery losses, gate charge losses, and output capacitance losses. These losses are also closely related to the characteristics of the driver circuit; a more powerful driver circuit will reduce the time the MOSFET operates in the linear region.

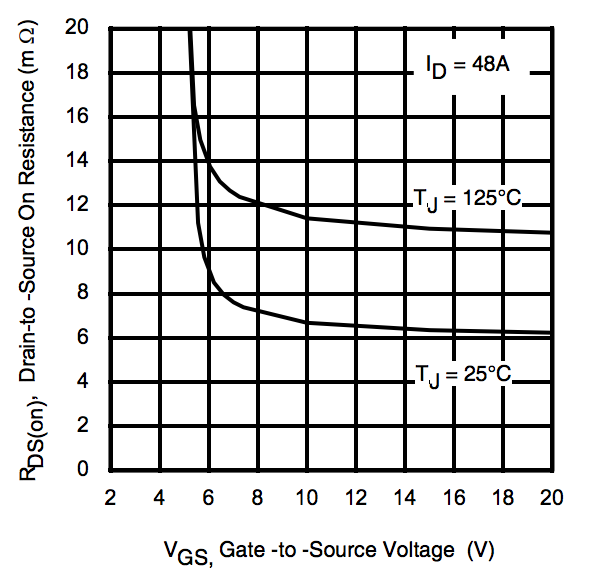
For the purposes of these analyses, a 2.4A peak driver pull-up current will be assumed, based on typical performances of the LTC4440 high-side high-speed driver IC (see figure 6) [10]. Furthermore, the MOSFET transitions through the linear region as the gate driver removes charge from the MOSFET’s gate. The charge at the gate is related to the MOSFET’s gate to source voltage by the curve shown in figure 7. Note that this is not a purely linear relationship, therefore for turn-on and turn-off losses in the MOSFET, it is useful to analize the MOSFET’s transition in three stages (corresponding to the three linear pieces of the curve in figure 7). Furthermore, the on-state resistance of the MOSFET’s channel is related to the gate-to-source voltage by the curve in figure 8.



**Figure 6 –** Peak Driver Pull-Up Current for the LTC-4440 High-Side MOSFET Driver.



**Figure 7 –** MOSFET Gate-to-Source Voltage vs. Gate Charge; Plateau due to the Miller Effect.



**Figure 8 –** MOSFET On-State Resistance vs. Gate-To-Source Voltage.

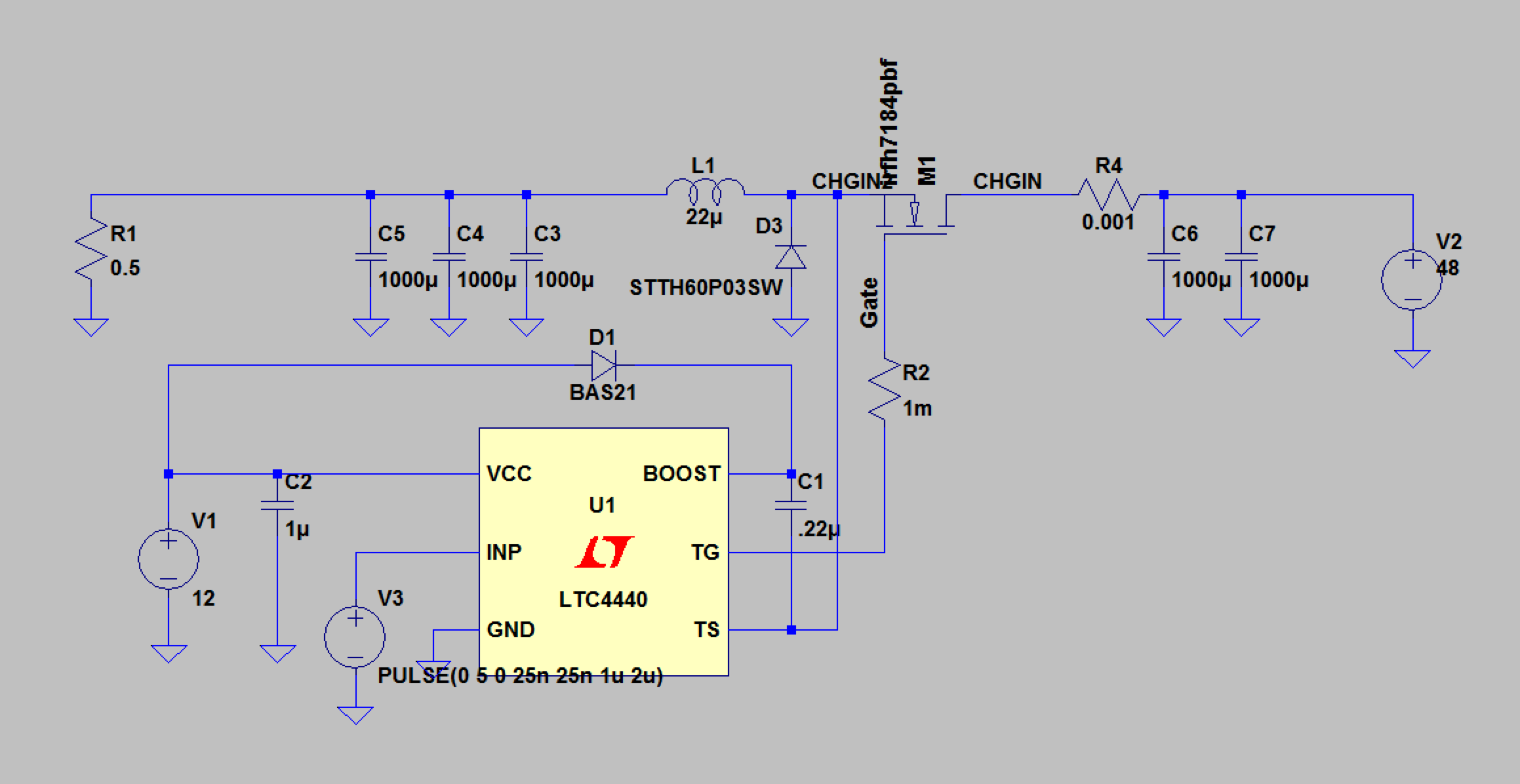
Thus with the curves in figures 7 and 8 it is possible to determine the MOSFET’s turn-on and turn-off losses [4]. First is the analysis of the three stages of the MOSFET’s turn-off period.

The first stage consists of the MOSFET’s transition from its high on-state gate-to-source voltage (sustained by the gate driver circuit and the MOSFET’s gate capacitance) to the knee in the curves of figures 7 and 8, which is VGS ≈ 6V. Figure shows that during this transition period RDS(on) remains approximately the same as in the MOSFET’s saturation operation region, therefore the losses here are the same as for the MOSFET’s on-state. This period of the switching is still key; however, as a significant portion of the gate charge is dissipated in this period, leading to the second stage of the turn-off period.

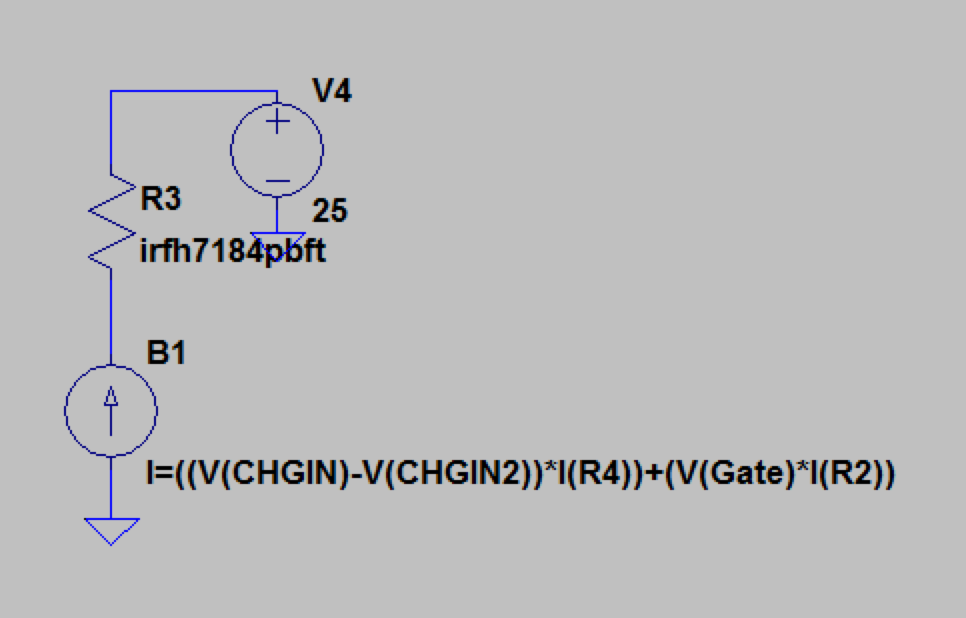
In the second stage of the MOSFET’s

**SPICE Model Simulations**

As there is a complex interdependence between switching losses, MOSFET heating, MOSFET gate charge, and MOSFET driver current, a SPICE model of the charger circuitry was created to simulate its electrical and thermal characteristics. The model simulations were run using the LTSpice software [9]. The simulation consisted of a buck-converter with models of real-world components, including the LTC4440 MOSFET driver IC. Additionally, MOSFET thermal-analysis was conducted under various circuit loading conditions using MOSFET thermal models provided by the manufacturers. The basic circuit network used for the electrical simulation is show in figure 5, while a basic thermal model is shown in figure 6. It is important to note that the components (such as the MOSFET thermal impedance) in some of these networks are actually macromodels of more complex networks not presented immediately in those figures.



**Figure 5 –** Buck Converter SPICE network in LTSpice.



**Figure 6 –** MOSFET Thermal model SPICE network in LTSpice.

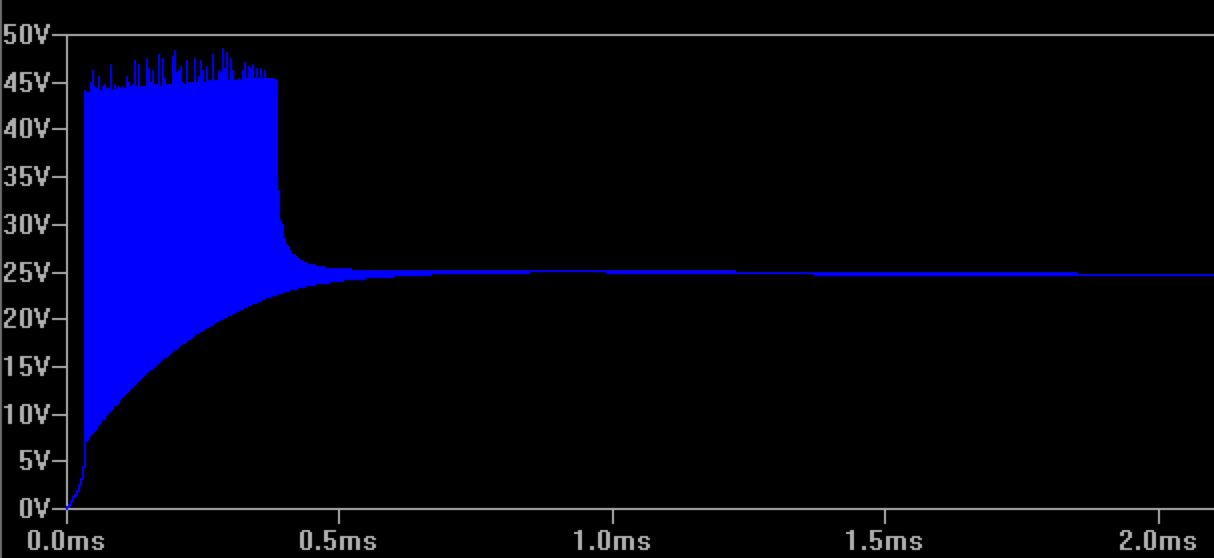
The initial model developed was a simple model for conducting baseline tests of various MOSFETs and for verifying model accuracy compared to expected results. Components of the electrical model include the non-ideal inductor L1, ideal filter capacitors with a non-zero ESR, ideal voltage sources for circuit power supply, non-ideal diode models, complex MOSFET models, and a macromodel of the driver IC provided by the manufacturer [10].

The thermal model varied depending on the data provided by the manufacturer. For the International Rectifier MOSFETs, a Foster RC thermal model was used for transient analysis, as the necessary parameters for this model were provided by the manufacturer [6][7][8]. This macromodel was represented by the two-terminal network element R3 (see figure 6). An arbitrary current source (B1) based on the power loss in the MOSFET was used to simulate a heat source, and a DC voltage source (V4) was used to model ambient temperature [11].

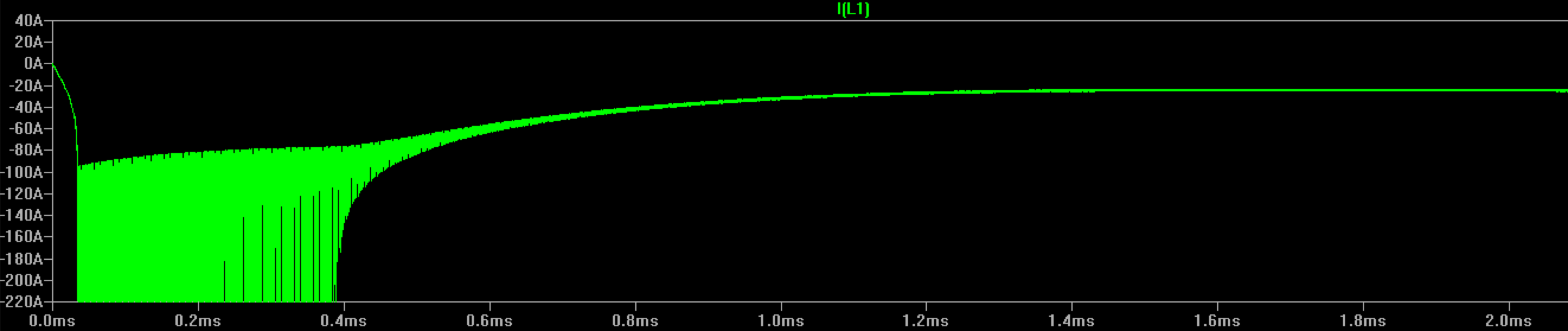
A vary of design parameters were tested using SPICE simulations, including inductance values, various MOSFETs, filter capacitance, and inductor saturation characteristics. The follow spice tests were conducted to characterize the circuit:

*Test 1: Basic Model Performance*

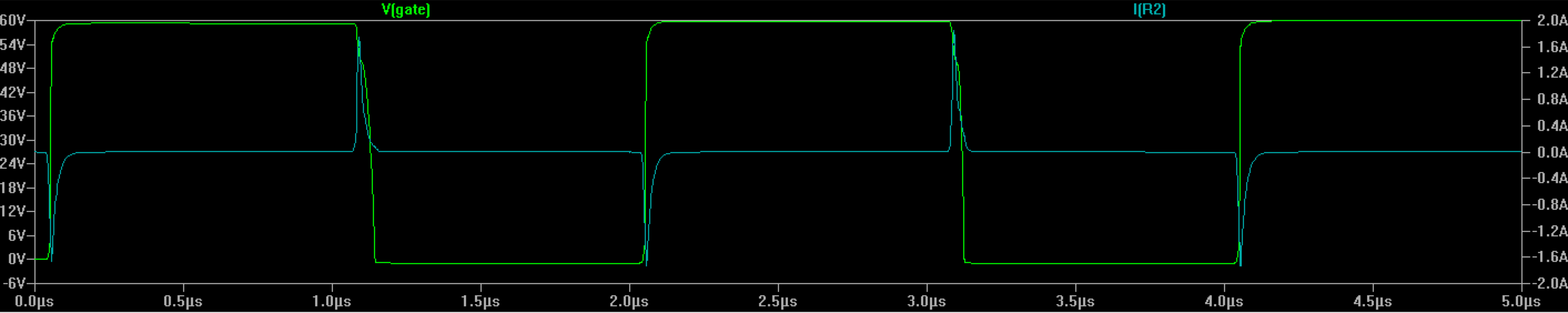
The first tests conducted were simple operation of the converter with a resistive load to verify that the simulation’s nets and models were configured properly. A 48V source was used as the input voltage, with a 500kHz driver signal at 50% duty cycle, in order to provide an expected 24V output to a 1.0-Ohm load. The results of the simulation are presented in figure 7 below.



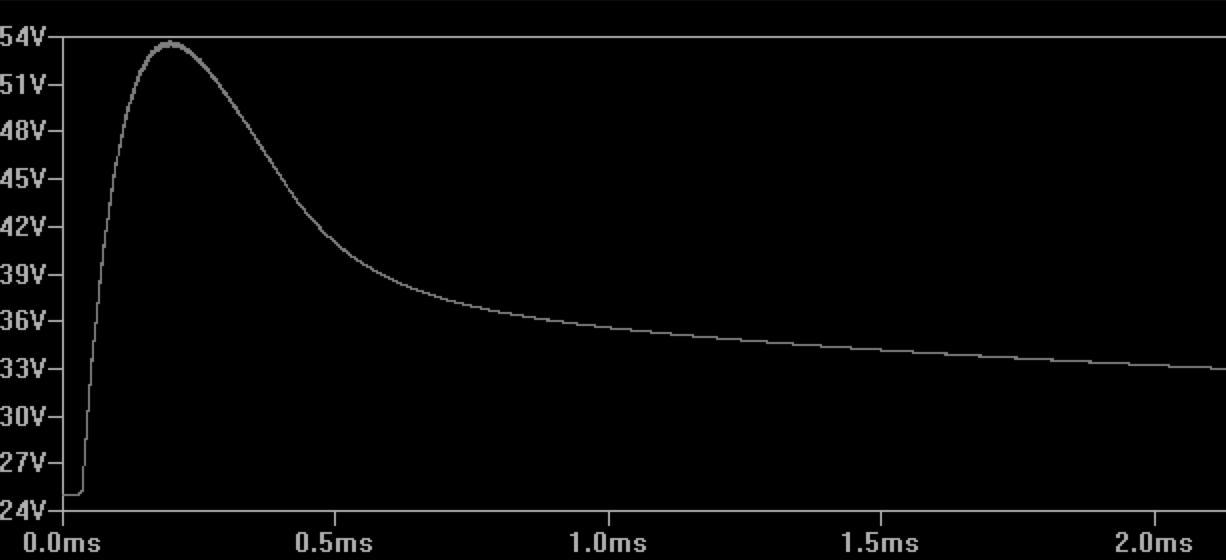
**Figure 7 –** Buck-Converter Output Voltage on Startup (Transient Analysis).



**Figure 8 –** Buck-Converter Inductor Current on Startup (Transient Analysis).



**Figure 9 –** Buck-Converter MOSFET Driver Current (Cyan Trace) and MOSFET Gate Voltage (Green Trace).



**Figure 10 –** MOSFET Junction Temperature in Degrees Celsius.



**Figure 11 –** Output Voltage for Various Driver Duty Cycles.

*Test 2: MOSFET Thermal Analysis in Various Load Conditions*

A basic thermal model for the

*Test 3: Basic MOSFET Performance Characterizations*

*Test 4: Load Transient Simulations*

**References**

1. West Coast Inductors 306 Series Datasheet. <http://wcmagnetics.wpengine.com/wp-content/uploads/2015/02/wcm306.pdf>
2. Coilcraft AGP4233 Series Power Inductor Datasheet. <http://coilcraft.com/pdfs/agp4233.pdf>
3. Coilcraft AGP4233-223ME Temperature Derating Curve. <http://coilcraft.com/misc/agp4233de.html>
4. “Estimating MOSFET Switching Losses Means Higher Performance Buck Converters.” Peter Markowski. EE Times. July 11, 2002. <http://www.eetimes.com/document.asp?doc_id=1225701>
5. Texas Instruments CSD18532KCS Datasheet. <http://www.ti.com/lit/ds/symlink/csd18532kcs.pdf>
6. International Rectifier IRFH7191 Datasheet. <http://www.irf.com/product-info/datasheets/data/irfh7184pbf.pdf>
7. International Rectifier IRFH7188 Datasheet. <http://www.irf.com/product-info/datasheets/data/irfh7188pbf.pdf>
8. International Rectifier IRFH7195 Datasheet. <http://www.irf.com/product-info/datasheets/data/irfh7195pbf.pdf>
9. Linear Technology’s LTSpice Simulation Software. <http://www.linear.com/solutions/ltspice>
10. Linear Technology’s LTC4440 High-Side MOSFET driver. [www.linear.com/product/LTC4440](http://www.linear.com/product/LTC4440)
11. NXP Semiconductors Application Note 11261: Using RC Thermal Models. <http://www.nxp.com/documents/application_note/AN11261.pdf>
12. “Power MOSFET Basics.” Vrej Barkhordarian. International Rectifier. <http://www.irf.com/technical-info/appnotes/mosfet.pdf>